



### 30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

80 A

#### **Features**

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V, I<sub>D</sub>@20A<6mΩ</li>
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_{D}@10A<9m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

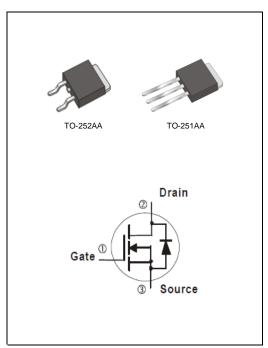


• Case: TO-251AA,TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• TO-251AA Approx. Weight: 0.0104 ounces, 0.297grams

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# $\textbf{Maximum Ratings and Thermal Characteristics} \; (T_A = 25 ^{\circ} \text{C unless otherwise noted})$

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	30	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20		
Continuous Drain Current (Note 4)	T <sub>C</sub> =25°C	l <sub>D</sub>	80	A	
	T <sub>C</sub> =100°C		50		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	320		
Power Dissipation	T <sub>C</sub> =25°C	Po	55	10/	
	T <sub>C</sub> =100°C		22	W	
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	I <sub>D</sub>	15	^	
	T <sub>A</sub> =70°C		12	Α	
Power Dissipation	T <sub>A</sub> =25°C	Б	2	W	
	T <sub>A</sub> =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	80	mJ	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	2.3	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1	1.6	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =10V, $I_D$ =20A	-	5.0	6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	-	6.6	9	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> =15V, I <sub>D</sub> =20A, V <sub>GS</sub> =4.5V <sup>(Note 2,3)</sup>	-	12	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.8	-	
Gate-Drain Charge	$Q_{gd}$		-	4.3	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1323	-	pF
Output Capacitance	Coss		-	219	-	
Reverse Transfer Capacitance	Crss	I=1.0IVINZ	-	136	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DS}$ =15V, $R_L$ =1 $\Omega$ , $V_{GS}$ =10V, $R_G$ =3.3 $\Omega$ (Note 2,3)	-	5	-	
Turn-On Rise Time	t <sub>r</sub>		-	42	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	36	-	
Turn-Off Fall Time	t <sub>f</sub>		-	5.5	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	,		-	-	80	А
Diode Forward Current	I <sub>S</sub>					
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.83	1	V

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<a>2%</a>.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =40A,  $V_{DD}$ =25V,  $V_{GS}$ =10V.
- 7. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

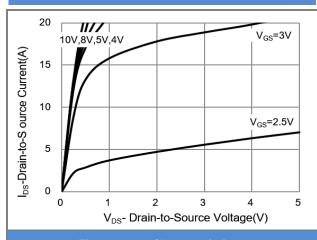
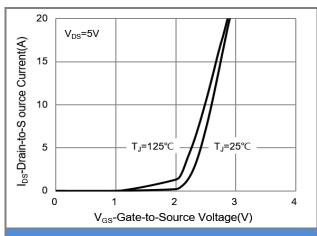


Fig.1 Output Characteristics



**Fig.2 Transfer Characteristics** 

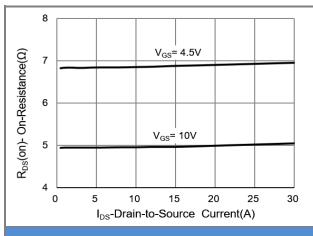


Fig.3 On-Resistance vs. Drain Current

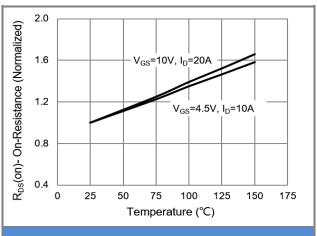


Fig.4 On-Resistance vs. Junction temperature

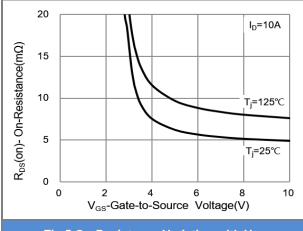


Fig.5 On-Resistance Variation with V<sub>GS</sub>

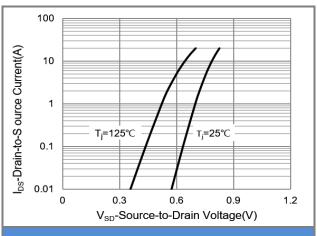


Fig.6 Source-Drain Diode Forward Voltage





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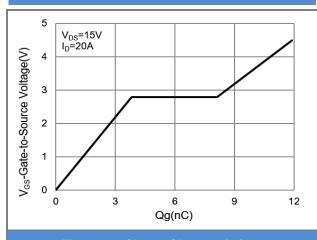


Fig.7 Gate-Charge Characteristics

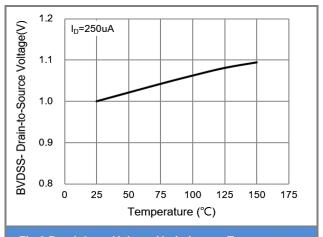


Fig.8 Breakdown Voltage Variation vs. Temperature

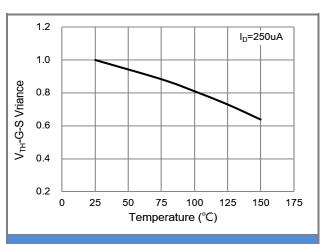


Fig.9 Threshold Voltage Variation with Temperature

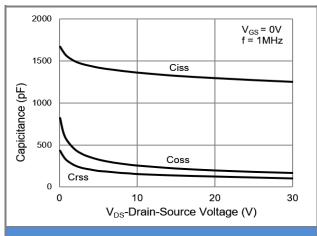


Fig.10 Capacitance vs. Drain-Source Voltage

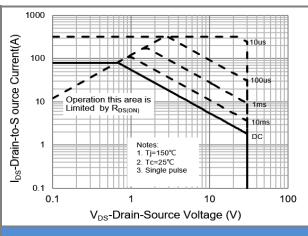


Fig.11 Maximum Safe Operating Area





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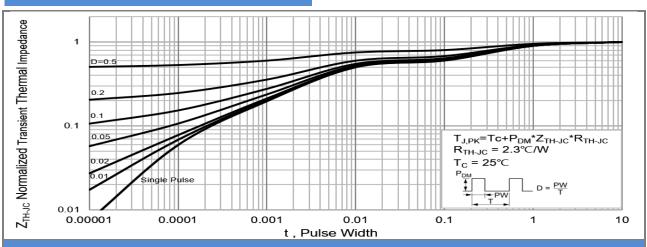
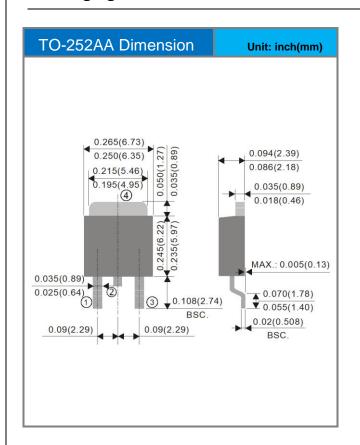


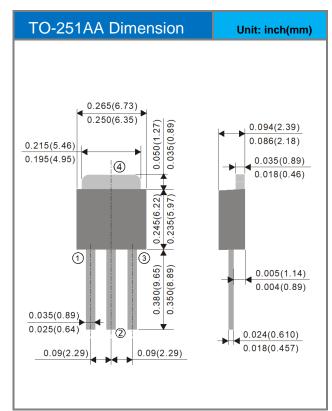
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





### **Packaging Information**





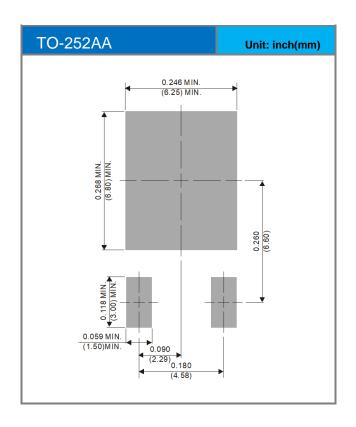




### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJU80N03_T0_00001	TO-251AA	80pcs / Tube	U80N03	Halogen free
PJD80N03_L2_00001	TO-252AA	3,000pcs / 13" reel	D80N03	Halogen free

### **Mounting Pad Layout**







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